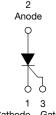


## Thyristor High Voltage, Surface Mountable Phase Control SCR, 16 A





TO-263AB (D<sup>2</sup>PAK)

	]
1	3
Cathode	Gate

PRODUCT SUMMAR	Υ
Package	TO-263AB (D <sup>2</sup> PAK)
Diode variation	Single SCR
I <sub>T(AV)</sub>	10 A
$V_{DRM}/V_{RRM}$	800 V, 1200 V
$V_{TM}$	1.4 V
I <sub>GT</sub>	60 mA
T <sub>J</sub>	- 40 °C to 125 °C

#### **FEATURES**

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Designed qualified according JEDEC-JESD47
- Compliant to RoHS Directive 2002/95/EC
- Halogen-free according to IEC 61249-2-21 definition





# RoHS

**HALOGEN** FREE

### **APPLICATIONS**

- Input rectification (soft start)
- · Vishay input diodes, switches and output rectifiers which are available in identical package outlines

### **DESCRIPTION**

The VS-16TTS..SPbF high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS								
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 μm) copper	2.5	3.5						
Aluminum IMS, R <sub>thCA</sub> = 15 °C/W	6.3	9.5	A					
Aluminum IMS with heatsink, R <sub>thCA</sub> = 5 °C/W	14.0	18.5						

#### Note

• T<sub>A</sub> = 55 °C, T<sub>J</sub> = 125 °C, footprint 300 mm<sup>2</sup>

MAJOR RATINGS AND CHARACTERISTICS									
SYMBOL	CHARACTERISTICS	VALUES	UNITS						
I <sub>T(AV)</sub>	Sinusoidal waveform	10	Λ.						
I <sub>RMS</sub>		16	A						
V <sub>RRM</sub> /V <sub>DRM</sub>		800/1200	V						
I <sub>TSM</sub>		200	A						
V <sub>T</sub>	10 A, T <sub>J</sub> = 25 °C	1.4	V						
dV/dt		500	V/µs						
dl/dt		150	A/µs						
TJ		- 40 to 125	°C						

VOLTAGE RATINGS									
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA						
VS-16TTS08SPbF	800	800	10						
VS-16TTS12SPbF	1200	1200	10						



ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS		
PARAMETER	STIVIBUL	TEST CONDITIONS	TYP.	MAX.	UNITS		
Maximum average on-state current	I <sub>T(AV)</sub>	$T_C = 98$ °C, 180° conduction, half sine wave	10				
Maximum RMS on-state current	I <sub>RMS</sub>		16		Α		
Maximum peak, one-cycle,	1	10 ms sine pulse, rated V <sub>RRM</sub> applied	170	)	A		
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied	200	)			
Maximum I <sup>2</sup> t for fusing	I <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied	144		- A <sup>2</sup> s		
Waxiinum i-t for fusing	1-1	10 ms sine pulse, no voltage reapplied	200				
Maximum l <sup>2</sup> √t for fusing	I²√t	t = 0.1 ms to 10 ms, no voltage reapplied		0	A²√s		
Maximum on-state voltage drop	$V_{TM}$	10 A, T <sub>J</sub> = 25 °C			V		
On-state slope resistance	r <sub>t</sub>	Tu = 125 °C	24.0	)	mΩ		
Threshold voltage	V <sub>T(TO)</sub>	1j = 125 G	1.1		V		
Maximum reverse and direct leakage current	1 /1	T <sub>J</sub> = 25 °C	0.5				
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	$V_R = Rated V_{RRM}/V_{DRM}$	10		mA		
Holding current	I <sub>H</sub>	Anode supply = 6 V, resistive load, initial I <sub>T</sub> = 1 A	-	100	IIIA		
Maximum latching current	ΙL	Anode supply = 6 V, resistive load		)			
Maximum rate of rise of off-state voltage	dV/dt		500	)	V/µs		
Maximum rate of rise of turned-on current	dl/dt			)	A/µs		

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P <sub>GM</sub>		8.0	W
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	90	
	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	60	mA
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	35	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	3.0	
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	V
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	V
Maximum DC gate voltage not to trigger	$V_{GD}$	T 105 °C V Detectively	0.25	
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value	2.0	mA

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9					
Typical reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 125 °C		μs				
Typical turn-off time	t <sub>q</sub>	1]=120 0	110					

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 40 to 125	°C			
Soldering temperature	Ts	For 10 s (1.6 mm from case)	240				
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.3	°C/W			
Typical thermal resistance, junction to ambient	R <sub>thJA</sub>	PCB mount (1)	40	C/VV			
Approximate weight			2	g			
Approximate weight			0.07	OZ.			
Moulting douise		Case style D <sup>2</sup> PAK (SMD-220)	16TTS08S				
Marking device		Case style D-PAN (SIVID-220)	16TTS12S				

#### Note

<sup>(1)</sup> When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm) copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994.

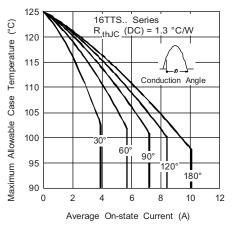


Fig. 1 - Current Rating Characteristics

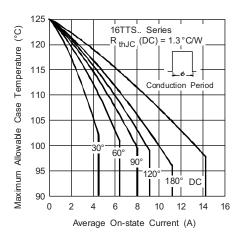


Fig. 2 - Current Rating Characteristics

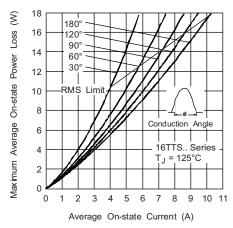


Fig. 3 - On-State Power Loss Characteristics

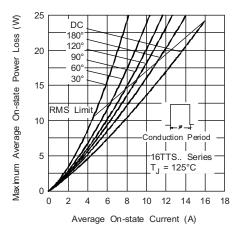


Fig. 4 - On-State Power Loss Characteristics

### www.vishay.com

### Vishay Semiconductors

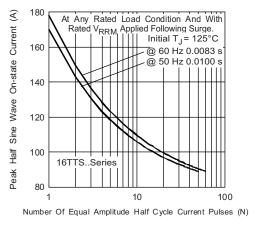


Fig. 5 - Maximum Non-Repetitive Surge Current

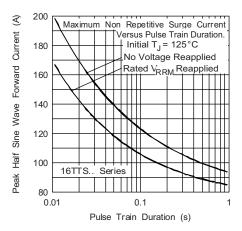


Fig. 6 - Maximum Non-Repetitive Surge Current

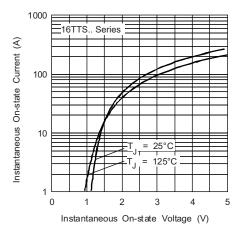


Fig. 7 - On-State Voltage Drop Characteristics

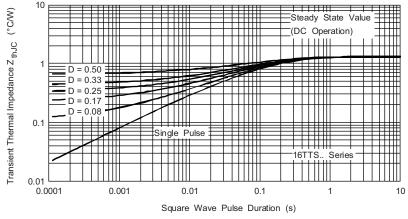


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

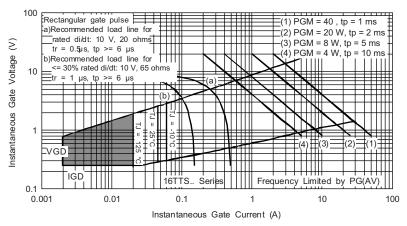
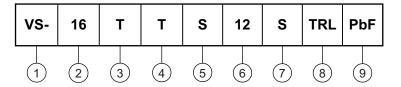


Fig. 9 - Gate Characteristics

### **ORDERING INFORMATION TABLE**

### Device code



1 - Vishay Semiconductors product

2 - Current rating

3 - Circuit configuration:

T = Single thyristor

4 - Package:

T = TO-220AC

5 - Type of silicon:

S = Standard recovery rectifier

6 - Voltage rating: Voltage code x 100 = V<sub>RRM</sub> ----

08 = 800 V 12 = 1200 V

7 - S = D<sup>2</sup>PAK version

8 - • None = Tube

• TRL = Tape and reel (left oriented)

• TRR = Tape and reel (right oriented)

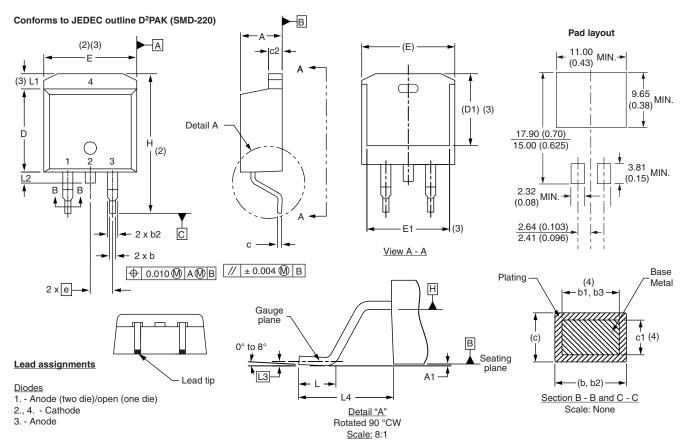
9 - PbF = Lead (Pb)-free and RoHS compliant

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95046				
Part marking information	www.vishay.com/doc?95054				
Packaging information	www.vishay.com/doc?95032				



## D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	STIVIBUL	MIN.	MAX.	MIN.	MAX
Α	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.31
A1	0.00	0.254	0.000	0.010		Е	9.65	10.67	0.380	0.42
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.34
b1	0.51	0.89	0.020	0.035	4	е	2.54	BSC	0.100	BSC
b2	1.14	1.78	0.045	0.070		Н	14.61	15.88	0.575	0.62
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.11
С	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.06
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.07
c2	1.14	1.65	0.045	0.065		L3	0.25	BSC	0.010	BSC
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.20

#### Notes

- $^{(1)}$  Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC outline TO-263AB

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MAX.

0.315

0.420

0.346

0.625

0.110 0.066

0.070

0.208

**NOTES** 

3

2, 3

3

3





Vishay

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